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November 2012

FJAFS1510A ESBC™ Rated NPN Power Transistor

Applications

- · High-Voltage and High-Speed Power Switches
- Emitter-Switched Bipolar/MOSFET Cascodes (ESBC™)
- Smart Meters, Smart Breakers, SMPS, HV Industrial Power Supplies
- · Motor Drivers and Ignition Drivers

ESBC Features (FDC655 MOSFET)

V _{CS(ON)}	Ic	Equiv. R _{CS(ON)}
0.426 V	6 A	$0.071~\Omega^{(1)}$

- · Low Equivalent On Resistance
- Very Fast Switch: 150 kHz
- · Avalanche Rated
- · Low Driving Capacitance, No Miller Capacitance
- Low Switching Losses
- Reliable HV switch: No False Triggering due to High dv/dt Transients

Description

The FJAFS1510A is a low-cost, high-performance power switch designed to provide optimal performance when used in an ESBC™ configuration in applications such as: power supplies, motor drivers, smart grid, or ignition switches. The power switch is designed to operate up to 1550 volts and up to 6amps, while providing exceptionally low on-resistance and very low switching losses.

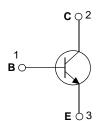
The ESBC™ switch is designed to be driven using off-the-shelf power supply controllers or drivers. The ESBC™ MOSFET is a low-voltage, low-cost, surface-mount device that combines low-input capacitance and fast switching. The ESBC™ configuration further minimizes the required driving power because it does not have Miller capacitance.

The FJAFS1510A provides exceptional reliability and a large operating range due to its square Reverse-Bias-Safe-Operating-Area (RBSOA) and rugged design. The device is avalanche rated and has no parasitic transistors so is not prone to static dv/dt failures.

The power switch is manufactured using a dedicated high-voltage bipolar process and is packaged in a high-voltage TO-3PF package.



Figure 1. Pin Configuration



B FJAFS1510A
FDC655

Figure 2. Internal Schematic Diagram Figure 3. ESBC Configuration⁽²⁾

Ordering Information

Part Number	Marking	Package	Packing Method	Remarks
FJAFS1510ATU	J1510A	TO-3PF	TUBE	

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Notes:

- 1. Figure of Merit.
- 2. Other Fairchild MOSFETs can be used in this ESBC application.

Absolute Maximum Ratings(3)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	1550	V
V _{CEO}	Collector-Emitter Voltage	750	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current (DC)	6	Α
P _C	Collector Dissipation (T _C = 25°C)	60	W
T _J	Operating and Junction Temperature Range	-55 to +125	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Notes:

3. Pulse Test: Pulse Width = 5 ms, Duty Cycle 10%.

Thermal Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Max.	Unit	
$R_{\theta jC}$	Thermal Resistance, Junction to Case	2.08	°C/W	

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current	$V_{CB} = 1400 \text{ V}, R_{BE} = 0$			100	μΑ
I _{CBO}	Collector Cut-off Current	$V_{CB} = 800 \text{ V}, I_{E} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 4 \text{ V}, I_{C} = 0$			100	μΑ
BV _{EBO}	Base-Emitter Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$	6			V
h _{FE1}	DC Current Gain	$V_{CE} = 5 \text{ V}, I_{C} = 0.5 \text{ A}$	15			
h _{FE2}	DC Current Gain	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$	7			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 6 \text{ A}, I_B = 1.5 \text{ A}, T_A = 125^{\circ}\text{C}$	Z	0.5		V
C _{ob}	Output Capacitance	$V_{CB} = 200 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		27		pF

ESBC Configured Electrical Characteristics (4) Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
f _T	Current Gain Bandwidth Product	I _C = 0.1 A, V _{CE} = 10 V		15.4		MHz
lt _f	Inductive Current Fall Time	$V_{GS} = 10 \text{ V}, R_{G} = 47 \Omega,$		115		ns
t _s	Inductive Storage Time	$V_{Clamp} = 500 \text{ V},$		670		ns
Vt _f	Inductive Voltage Fall Time	$I_C=1 \text{ Å}, I_B=0.1 \text{ A}, h_{FE}=10,$		160		ns
Vt _r	Inductive Voltage Rise Time	$L_C = 1 \text{ mH},$		95		ns
t _c	Inductive Crossover Time	SRF = 350 kHz		130		ns
lt _f	Inductive Current Fall Time	$V_{GS} = 10 \text{ V}, R_{G} = 47 \Omega,$		12.5		ns
t _s	Inductive Storage Time	V _{Clamp} = 500 V,		1100		ns
Vt _f	Inductive Voltage Fall Time	$I_C = 5 \text{ A}, I_B = 1 \text{ A}, h_{FE} = 5,$		68		ns
Vt _r	Inductive Voltage Rise Time	$L_C = 1 \text{ mH},$		110		ns
t _c	Inductive Crossover Time	SRF = 350 kHz		150		ns
V _{CSW}	Maximum Collector Source Voltage at Turn-off without Snubber	$h_{FE} = 5, I_{C} = 6 A$	1550			V
I _{GS(OS)}	Gate-Source Leakage Current	$V_{GS} = \pm 20 \text{ V}$		1.0		nA
V _{CS(ON)}	Collector-Source On	$V_{GS} = 10 \text{ V}, I_C = 6 \text{ A}, I_B = 2 \text{ A}, h_{FE} = 3$		0.426		V
. ,	Voltage	$V_{GS} = 10 \text{ V}, I_C = 4 \text{ A}, I_B = 1.3 \text{ A}, h_{FE} = 3$		0.213		V
		$V_{GS} = 10 \text{ V}, I_C = 2 \text{ A}, I_B = 0.67 \text{ A}, h_{FE} = 3$		0.162		V
		$V_{GS} = 10 \text{ V}, I_{C} = 1 \text{ A}, I_{B} = 0.2 \text{ A}, h_{FF} = 5$		0.141		V
V _{GS(th)}	Gate Threshold Voltage	V _{BS} = V _{GS} . I _B = 250 μA		1.9		V
C _{iss}	Input Capacitance (V _{GS} =V _{CB} =0)	V _{CS} = 25 V, f = 1 MHz		470		pF
Q _{GS(tot)}		$V_{GS} = 10 \text{ V}, I_C = 6 \text{ A}, V_{CS} = 25 \text{ V}$		9		nC
r _{DS(ON)}	Static Drain to Source	$V_{GS} = 10 \text{ V}, I_D = 6.3 \text{ A}$		21		mΩ
20(0.1)	On Resistance	V _{GS} = 10 V, I _D = 6.3 A, T _A = 125°C		30		mΩ
		V _{GS} = 4.5 V, I _D = 5.5 A		26		mΩ

Notes:

4. Used typical FDC655 MOSFET specifications in table. Table could vary if other Fairchild MOSFETs are used.

Typical Performance Characteristics

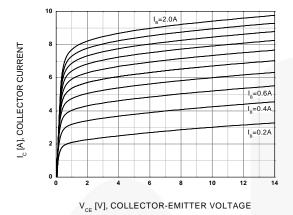


Figure 4. Static Characteristic

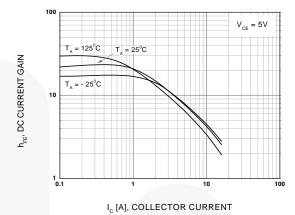


Figure 5. DC current Gain

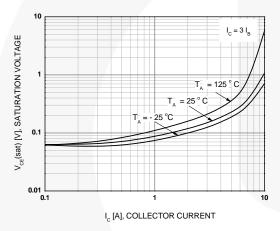


Figure 6. Collector-Emitter Saturation Voltage h_{FE} =3

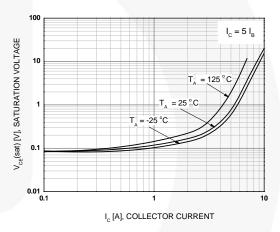


Figure 7. Collector-Emitter Saturation Voltage h_{FE} =5

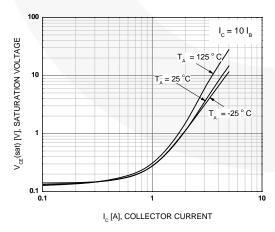


Figure 8. Collector-Emitter Saturation Voltage h_{FE} =10

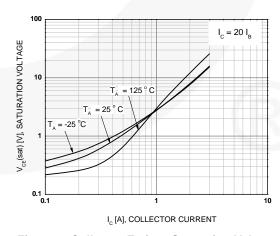


Figure 9. Collector-Emitter Saturation Voltage h_{FE} =20

Typical Performance Characteristics (Continued)

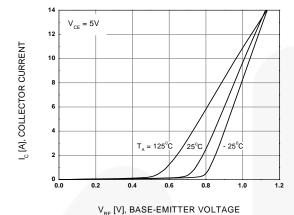


Figure 10. Base-Emitter On Voltage

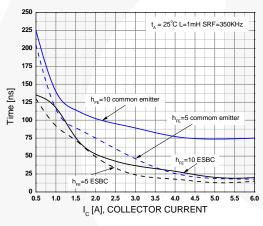


Figure 12. Inductive Load Collector Current Fall-time (t_f)

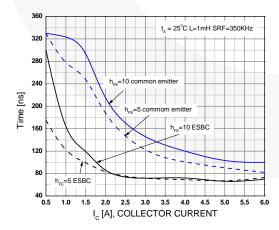


Figure 14. Inductive Load Collector Voltage Fall-time (t_f)

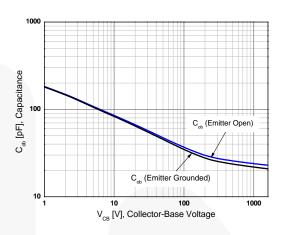


Figure 11. Capacitance

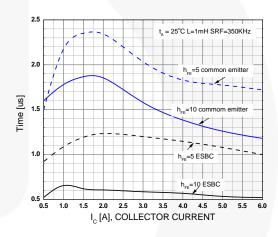


Figure 13. Inductive Load Collector Current Storage time (t_{stg})

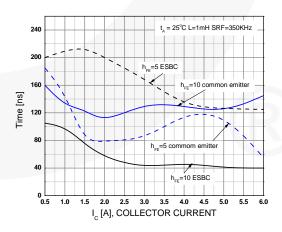


Figure 15. Inductive Load Collector Voltage Rise-time (t_r)

Typical Performance Characteristics (Continued)

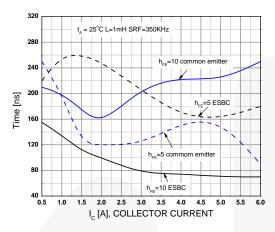


Figure 16. Inductive Load Collector Current/Voltage Crossover (t_c)

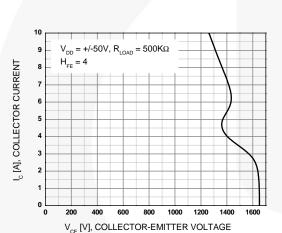


Figure 18. ESBC RBSOA

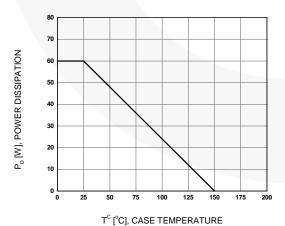


Figure 20. Power Derating

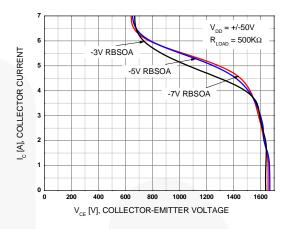


Figure 17. Reverse Bias Safe Operating Area

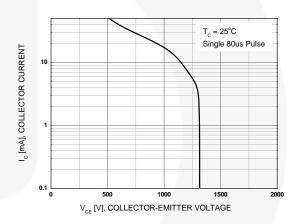


Figure 19. Forward Bias Safe Operating Area

Test Circuits

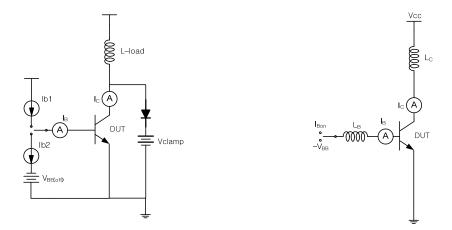


Figure 21. Test Circuit For Inductive Load and Reverse Bias Safe Operating

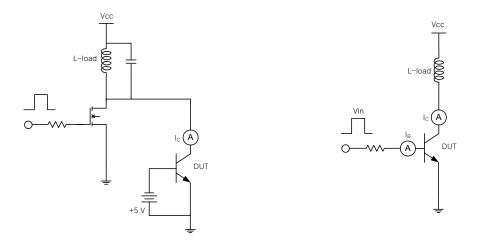


Figure 22. Energy Rating Test Circuit

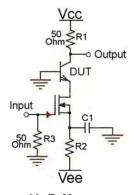


Figure 23. Ft Measurement

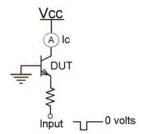


Figure 24. FBSOA

Test Circuits (Continued)

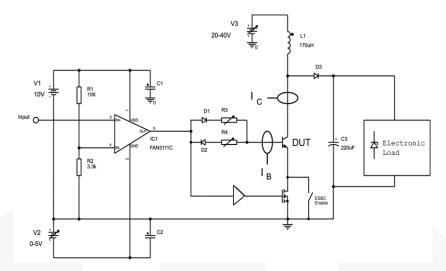


Figure 25. Simplified Saturated Switch Driver Circuit

Functional Test Waveforms

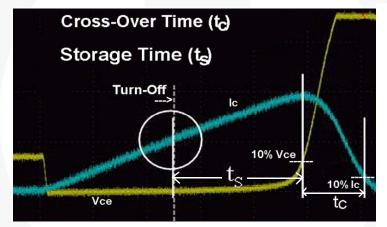


Figure 26. Crossover Time Measurement

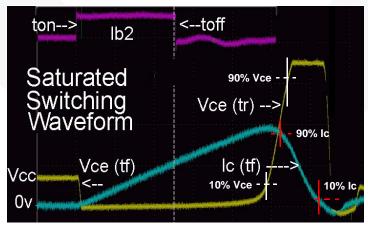


Figure 27. Saturated Switching Waveform

Functional Test Waveforms (Continued)

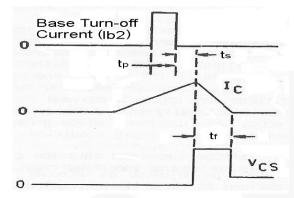


Figure 28. Storage Time - Common Emitter Base turn off (lb2) to $I_{\rm C}$ Fall-time

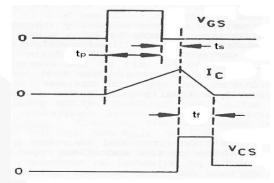
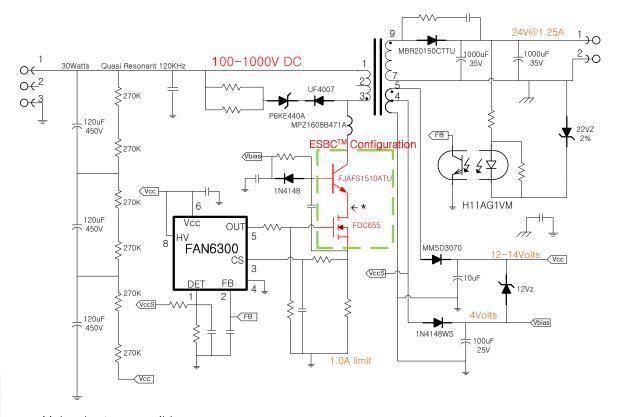


Figure 29. Storage Time - ESBC FET Gate (off) to I_C Fall-time

Very Wide Input Voltage Range Supply

- 30 W; Secondary-Side Regulation: 3 Capacitor Input; Quasi Resonant



* Make short as possible

Figure 30. Very Wide Input Voltage Range Supply

Driving ESBC Switches

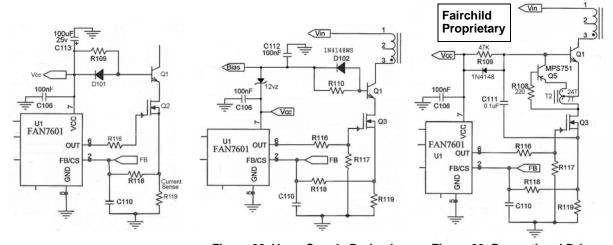


Figure 31. V_{CC} Derived

Figure 32. V_{BIAS} Supply Derived

Figure 33. Proportional Drive

Physical Dimensions

TO-3PF

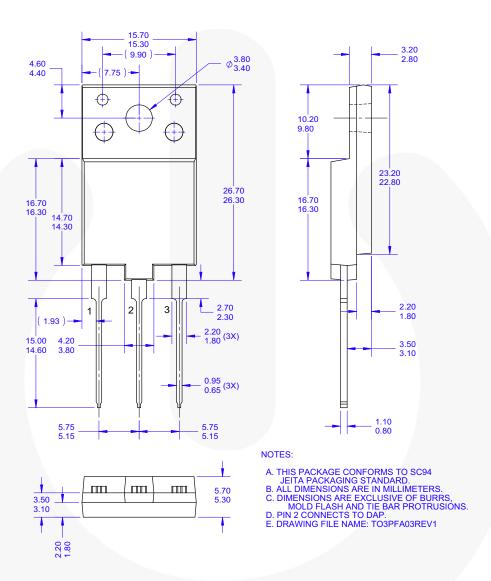


Figure 34. TO-3PF, 3 Leads, Molded, Full Pack

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